

OptiMOS™3 Power-Transistor

Features

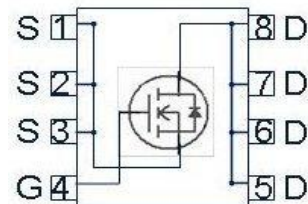
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Superior thermal resistance
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	60	V
$R_{DS(on),max}$	11	mΩ
I_D	50	A



Type	BSC110N06NS3 G
	
Package	PG-TDSON-8
Marking	110N06NS



Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$	50	A
		$V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$	33	
		$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$, $R_{thJA}=50\text{K/W}^{2)}$	12	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	200	
Avalanche energy, single pulse ⁴⁾	E_{AS}	$I_D=50\text{ A}$, $R_{GS}=25\text{ Ω}$	22	mJ
Gate source voltage	V_{GS}		±20	V

¹⁾ J-STD20 and JESD22

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See figure 3 for more detailed information

⁴⁾ See figure 13 for more detailed information

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	50	W
		$T_A=25\text{ °C}$, $R_{\text{thJA}}=50\text{ K/W}^{(2)}$	2.5	
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	2.5	K/W
Device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ⁽²⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}$, $I_{\text{D}}=1\text{ mA}$	60	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=23\text{ }\mu\text{A}$	2	3	4	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=60\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{\text{DS}}=60\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}$, $V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}$, $I_{\text{D}}=50\text{ A}$	-	9.0	11	mΩ
Gate resistance	R_{G}		-	1.3	-	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$, $I_{\text{D}}=50\text{ A}$	25	50	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$ $f=1\text{ MHz}$	-	2000	2700	pF
Output capacitance	C_{oss}		-	440	590	
Reverse transfer capacitance	C_{rss}		-	17	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$ $I_D=50\text{ A}, R_{G,ext}=3\ \Omega$	-	10	-	ns
Rise time	t_r		-	77	-	
Turn-off delay time	$t_{d(off)}$		-	14	-	
Fall time	t_f		-	6	-	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=30\text{ V}, I_D=50\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	12	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	6	-	
Gate to drain charge	Q_{gd}		-	3	-	
Switching charge	Q_{sw}		-	8	-	
Gate charge total	Q_g		-	25	33	
Gate plateau voltage	$V_{plateau}$		-	5.9	-	V
Output charge	Q_{oss}	$V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$	-	20	27	

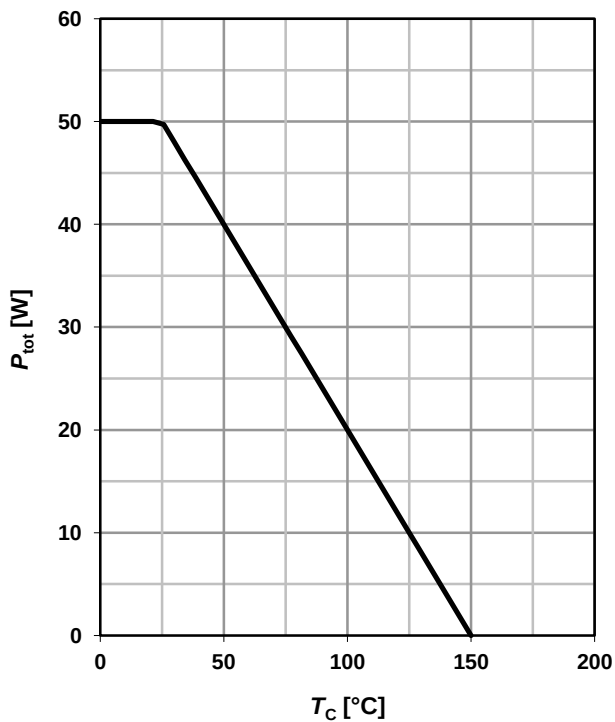
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ °C}$	-	-	53	A
Diode pulse current	$I_{S,pulse}$		-	-	212	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=50\text{ A},$ $T_J=25\text{ °C}$	-	0.95	1.2	V
Reverse recovery time	t_{rr}	$V_R=30\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	36	-	ns
Reverse recovery charge	Q_{rr}		-	38	-	nC

⁵⁾ See figure 16 for gate charge parameter definition

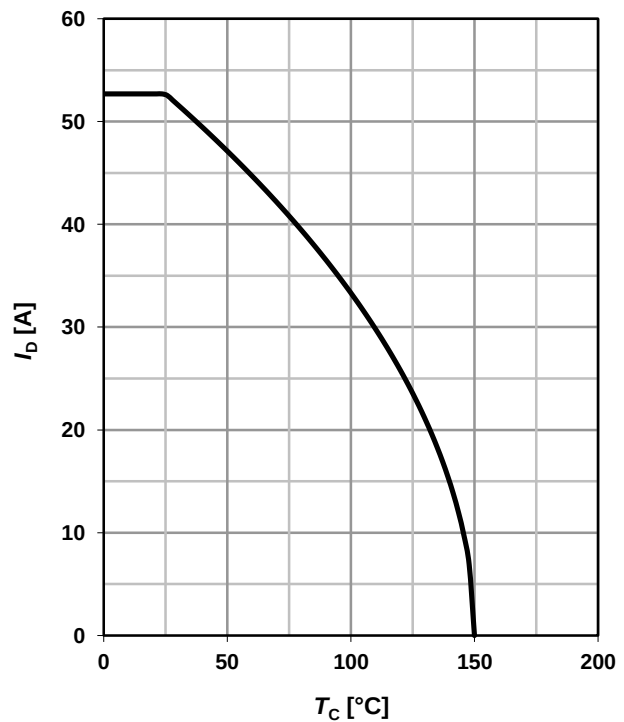
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Drain current

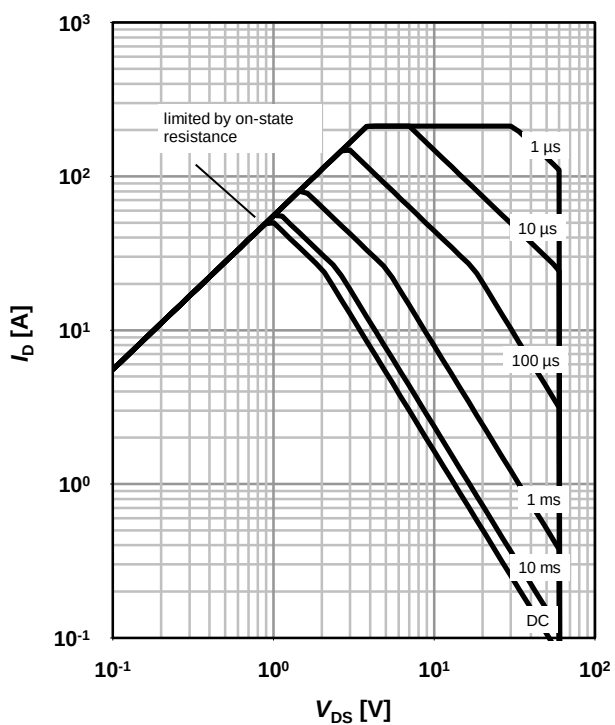
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

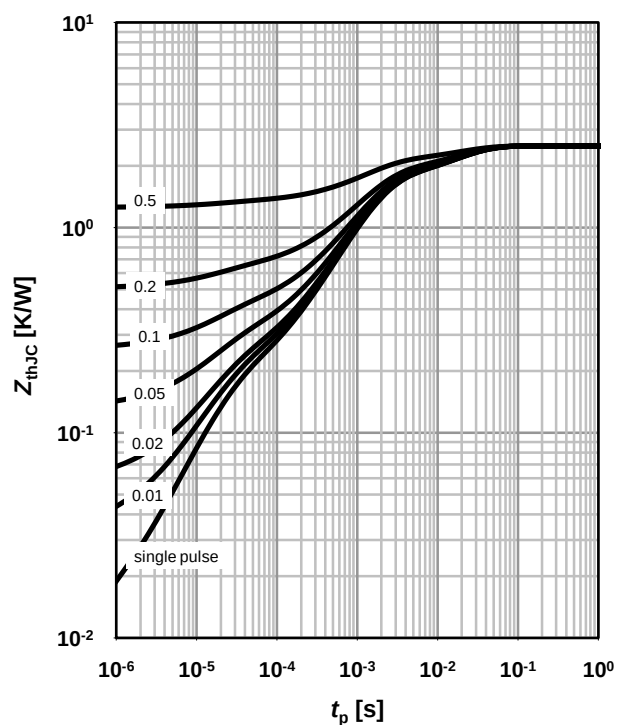
parameter: t_p



4 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

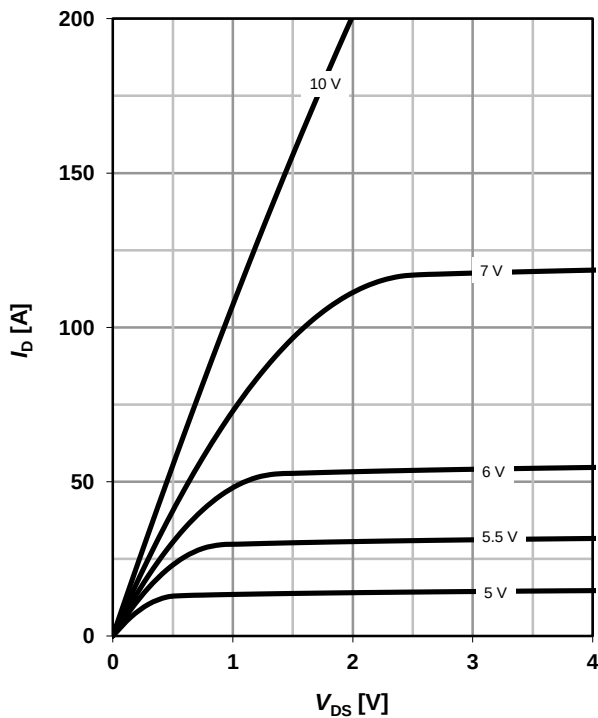
parameter: $D = t_p / T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

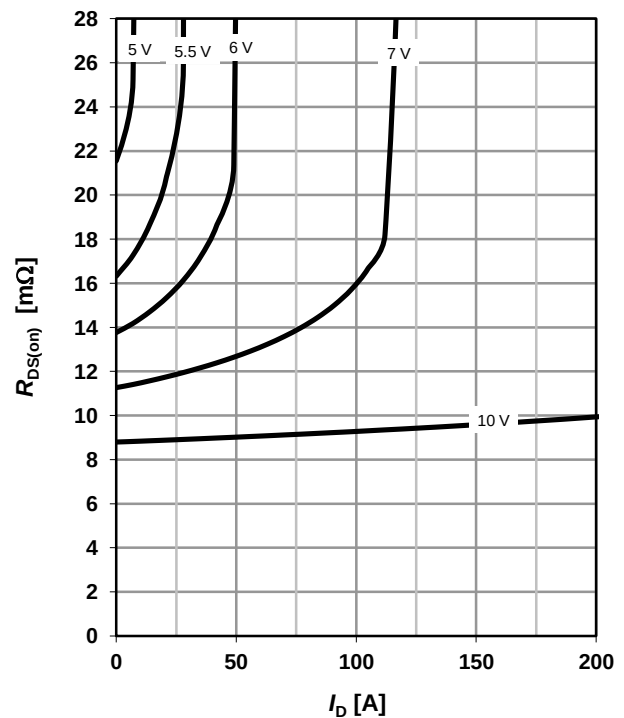
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

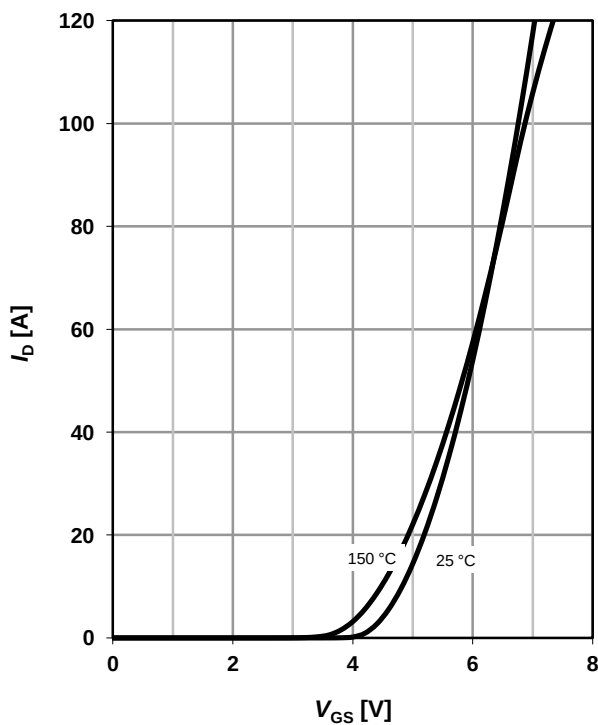
parameter: V_{GS}



7 Typ. transfer characteristics

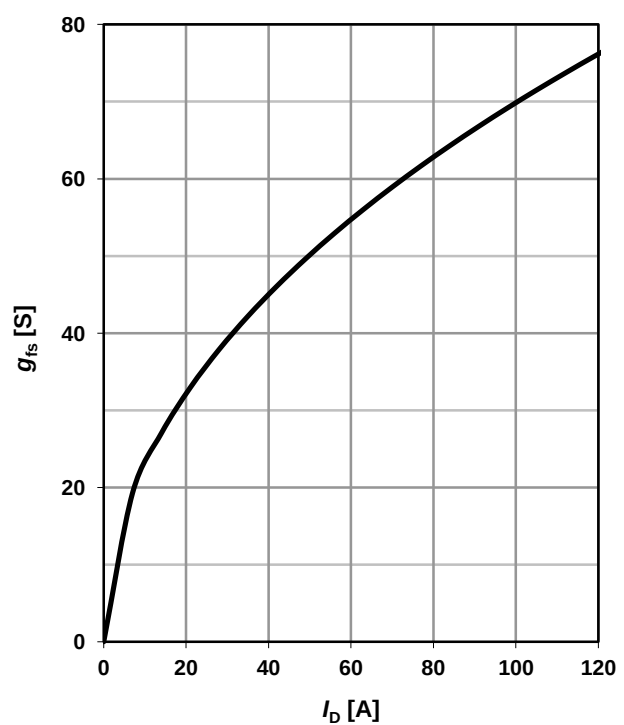
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



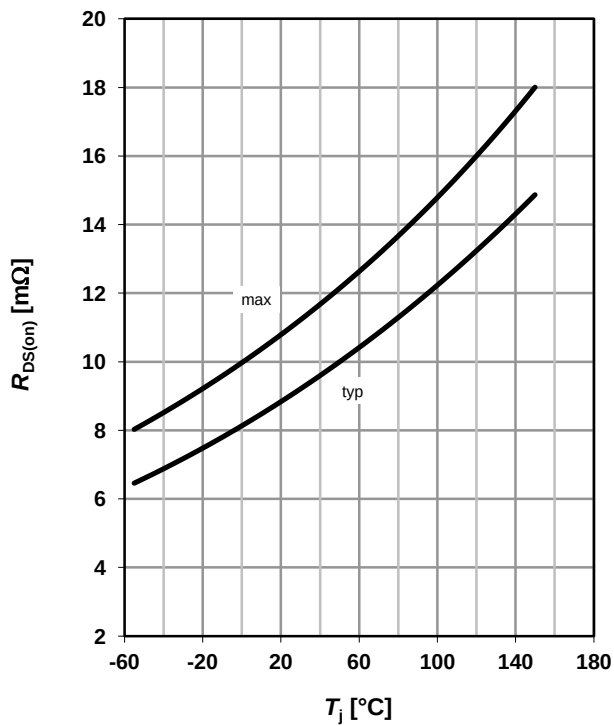
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$



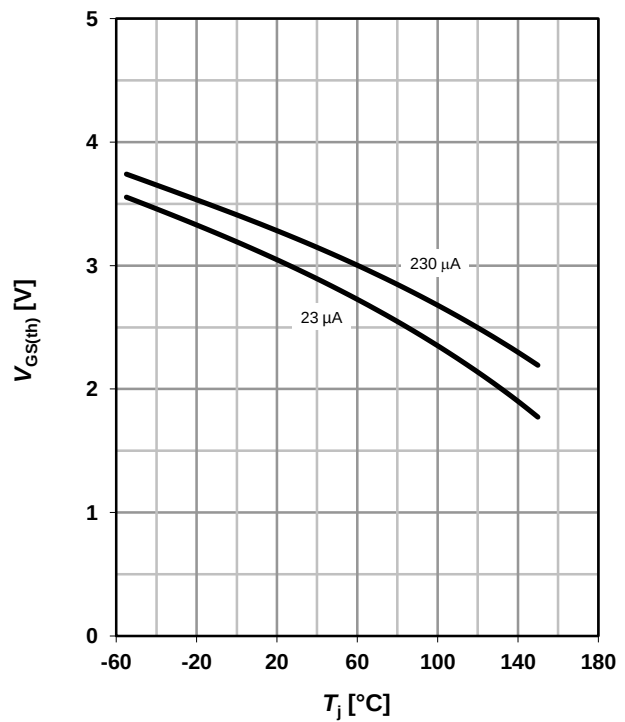
9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j); I_D = 50 \text{ A}; V_{GS} = 10 \text{ V}$$



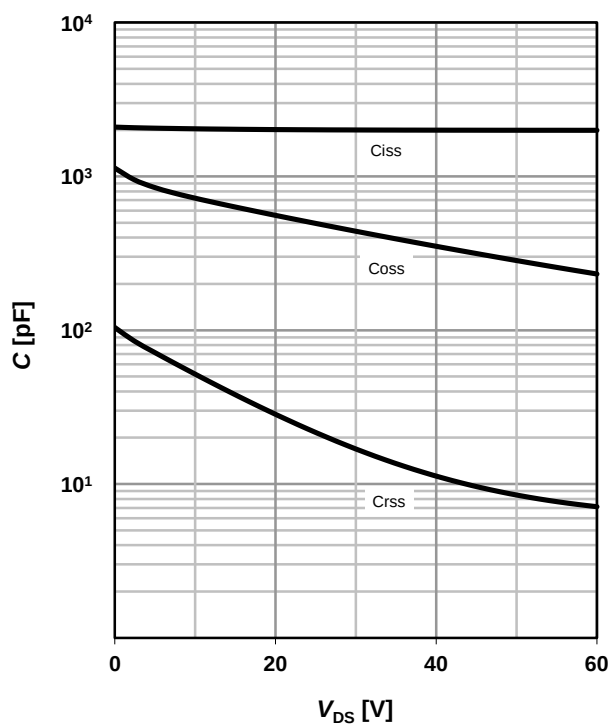
10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$



11 Typ. capacitances

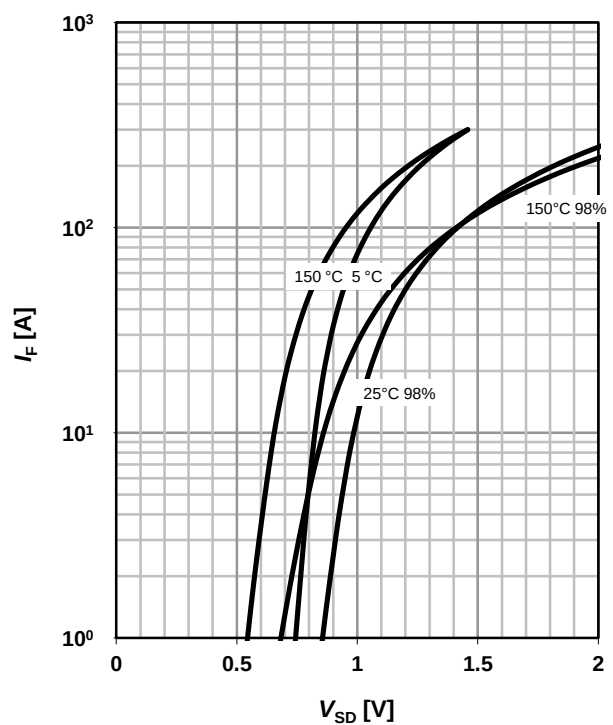
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

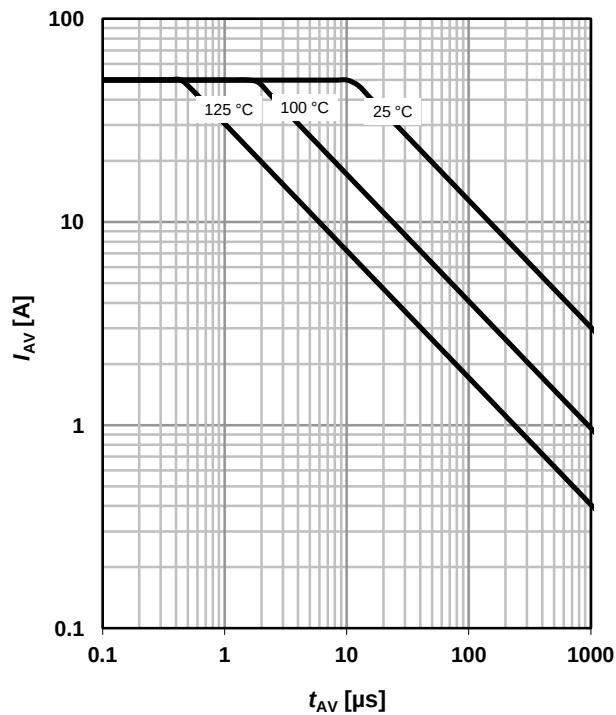
parameter: T_j



13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

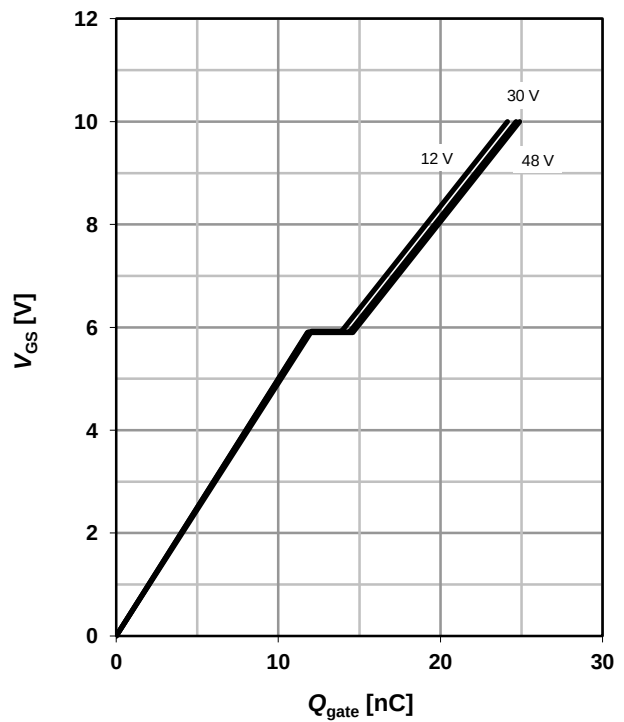
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

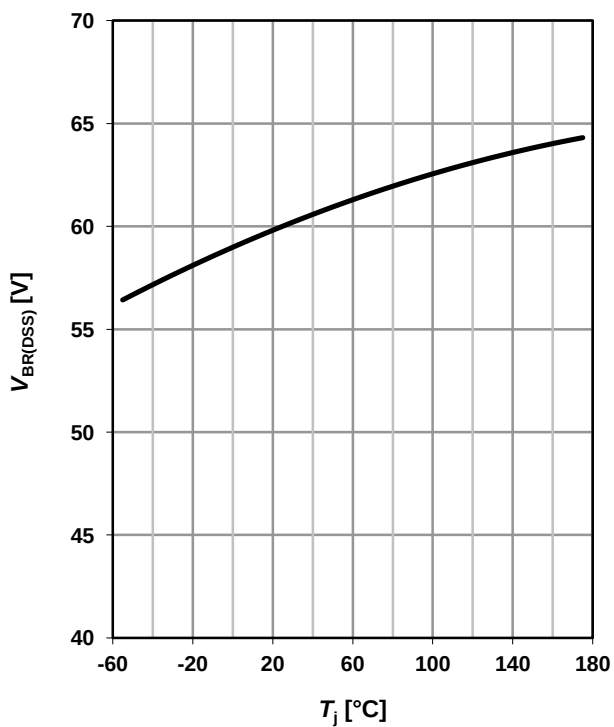
$$V_{GS}=f(Q_{\text{gate}}); I_D=50\ \text{A pulsed}$$

parameter: V_{DD}

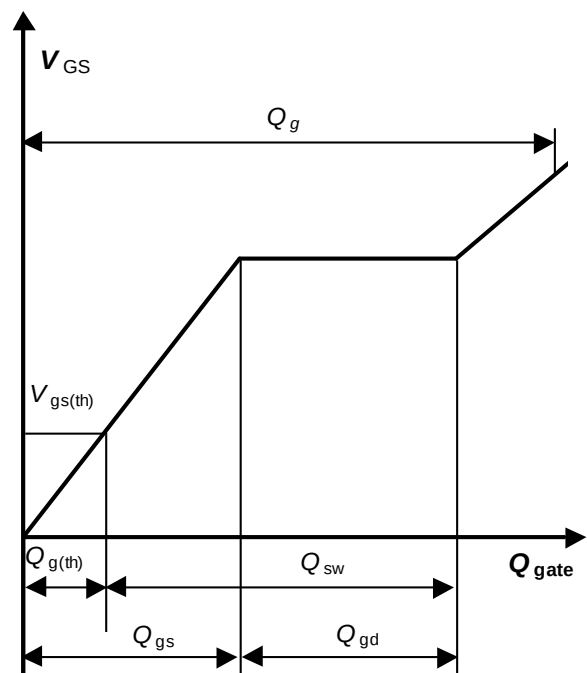


15 Drain-source breakdown voltage

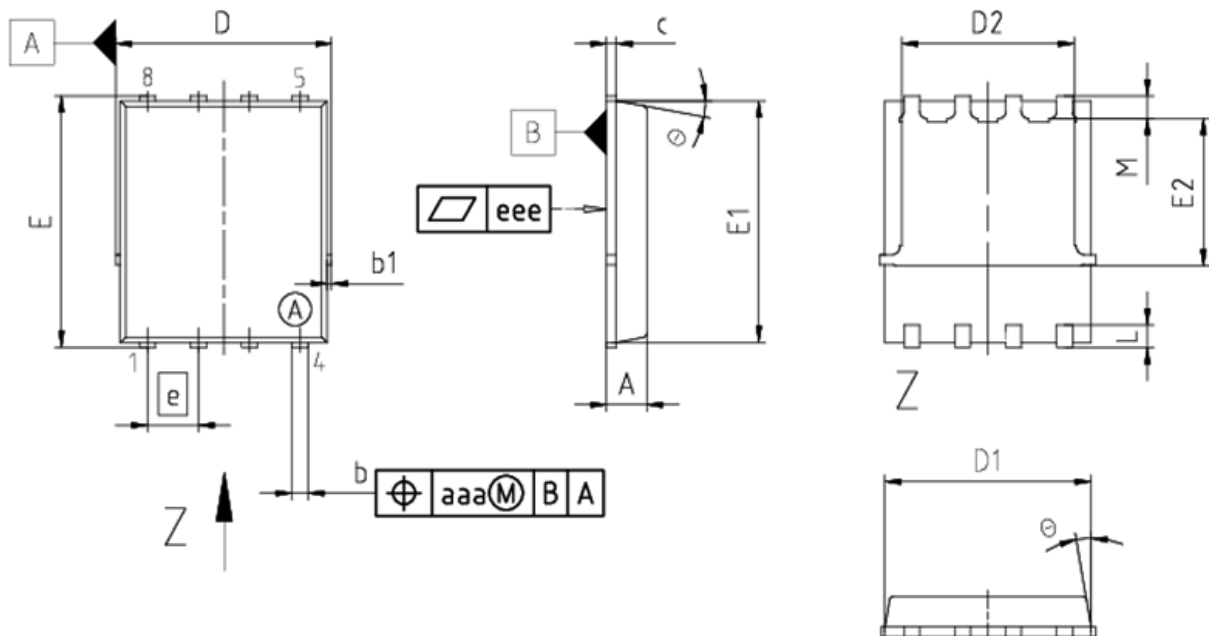
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



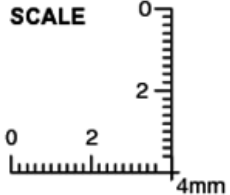
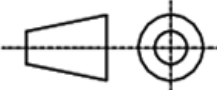
16 Gate charge waveforms



PG-TDSON-8 (SuperSO8)



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
ø	8.5°	12°
aaa	0.25	
eee	0.08	

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